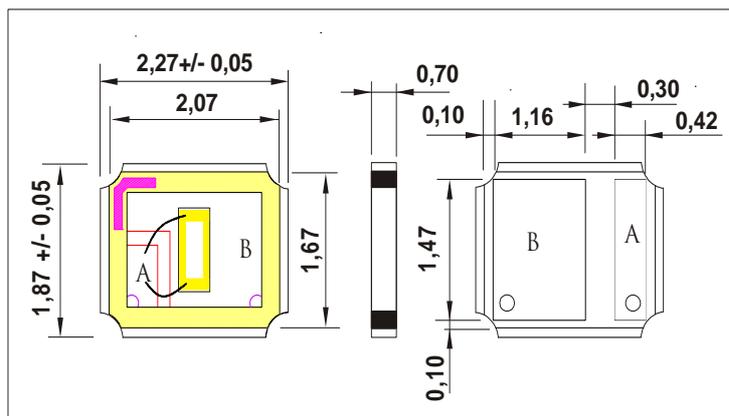


IR-LED - Edged Corner Bonded
870nm
FQA25586AVC
Features

- * Standard design LED for general purpose
Based on double hetero structure of GaAlAs
- * Fast switching time : typical <40ns
- * LTCC-Package with Ag-slug technology
for low thermal resistance
- * High-puls current drivable
- * Edged bonded chip design with pad and wire free emitting center
- * Application : Open-Air communication / IrDa
IR-Flash-Lights
Medical instruments
Light interrupter and switches


Electrical and optical characteristics and absolute maximum ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	MIN	Typ	MAX	Unit	Test conditions
I _F	DC Forward current			100	mA	R _{therm} < 100 K/W
I _{PEAK}	Peak Forward current			3000	mA	T _p < 10μsec. ; T=1:200 ; R _{therm} < 50 K/W
V _F	Forward Voltage	1,15	1,5	2,1	V	I _F = 100mA
V _R	Reverse Voltage	5			V	I _{rev} = 100μA
λ _{Peak}	Peak Wavelength	860	870	885	nm	I _F = 50mA
Δλ _{0,5}	Bandwidth of half power	25	30		nm	I _F = 50mA
t _f	Fall time		40		ns	I _F = 100mA
t _r	Rise time		40		ns	I _F = 100mA
Φ _E	Total Power Output	35		65	mW	I _F = 100mA
I _E	Radiant Intensity	10			mW/sr	I _F = 100mA
A	Chip size		0,31		mm ²	Chip size : 870μmX360μm
2Φ _{0,5}	Emission Angle		130		deg.	Φ _E = 50%
TK _{VF}	Temp.Coeff. of Forward Voltage		- 2		mV/K	*
TK _F	Temp.Coeff. of Radiant Power		- 0,4		%/K	*
T _{Operating}	Operating Temperature	- 25		85	°C	
T _{Storage}	Storage Temperature	- 25		85	°C	
T _{Soldering}	Soldering Temperature			260	°C	5mm from case @5 sec.
Θ _{j-PIN}	Thermal Resistance			50	K/W	
P _{tot}	Total Power Dissipation			220	mW	derate above 45°C 3,5mW/K

* values only for information

All optical measurements are based on accuracy of +/-11%.

R_{therm} : heat sink capability by PCB or other constructions

Order Informations :

FQA25586AVC-TR Tape & Reel

Fietje reserves the right to make changes at any time in order to improve design and to supply the best product possible, contact Fietje for latest device specification sheets before using.